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Roll No

EC - 304

B.E. III Semester

Examination, December 2012

Electronics devices

Time: Three Hours

Maximum Marks: 70/100

Note: 1. Attempt any Five questions.

- 2. All questions carry equal marks.
- a) Explain the behaviour of a Pn junction under the following conditions:
 - i) Unbiased
 - ii) Forward biased and
 - iii) Reverse biased

Sketch the relevant characteristics.

- b) Define the following terms with reference to a semiconductor diode
 - i) Barrier potential
 - ii) Cut in voltage
 - iii) The reverse saturation current
 - iv) Depletion layer
 - v) Dynamic forward resistance

PTO

- a) Draw the VI characteristic of a semiconductor diode. Give
 the equation for the current in semiconductor diode and
 with the help of this equation explain in detail VI
 characteristic of a semiconductor diode.
 - What is Hall effect and Hall coefficient explain? Describe the applications of Hall effect.
- a) Explain the working of a zener diode. Describe with the help of a circuit diagram, the working of a voltage regulator using zener diode.
 - b) Describe the working and applications of following diodes
 - i) Varactor diode
 - ii) LED
- a) Draw positive clipper circuit. Show input and output waveform and explain its working.
 - Draw and explain the diode clamper or dc restorer. Show input and output waveforms and briefly explain the operation of the circuit.
- 5. a) Draw a schematic diagram of a transistor indicating the different currents define α and β of a transistor and obtain the relation between them.
 - b) How will you draw dc load line on the output characteristics of a transistor. What is its importance? Define operating point. Also explain cut off, active and saturation region.
 - 6. a) Give the functional diagram, symbol and characteristics graph of UJT. Also describe its principle of operation.

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- b) What are the different transistor configurations for a transistor. Identify the input and output current in each of them and write the expressions for the current gains. Also compare the characteristics of the transistor in three possible configurations.
- 7. a) Describe the construction and operation of FET. What is the difference between N channel and P channel JFET.
 - b) Draw the transfer characteristics of JFET and explain it in detail.
- a) Give the construction, operation, characteristics and applications of enhancement MOSFET.
 - b) Compare the following:
 - i) FET and BJT
 - ii) FET and MOSFET
 - iii) Enhancement MOSFET and depletion MOSFET
- 9. Write short notes on any two of the following:
 - i) Application of diode as rectifier
 - ii) Power dissipation in transistor
 - iii) Photo transistor
 - iv) Tunnel diode
 - v) Transition and diffusion capacitance.
